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## \*BIBDATASHEET\*

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## \*\* CONTINUING DATA \*\*\*\*\*

This application is a DIV of 10/261,487 10/02/2002 PAT 6,756,611 *TD*which is a DIV of 09/986,332 11/08/2001 *TD*which is a CON of 09/603,437 06/23/2000 ABN *TD*which is a DIV of 09/202,141 12/09/1998 PAT 6,153,010 *TD*which is a 371 of PCT/JP98/01640 04/09/1998 *TD*

## \*\* FOREIGN APPLICATIONS \*\*\*\*\*

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Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no	STATE OR	SHEETS	TOTAL	INDEPENDENT
35 USC 119 (a-d) conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance	COUNTRY	DRAWING	CLAIMS	CLAIMS
Verified and Acknowledged Examiner's Signature <i>[Signature]</i> Initials <i>TD</i>	JAPAN	8	27	2

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## TITLE

Nitride semiconductor growth method, nitride semiconductor substrate and nitride semiconductor device